STB23NM60N-STF23NM60N
STI23NM60N-STP23NM60N-STW23NM60N

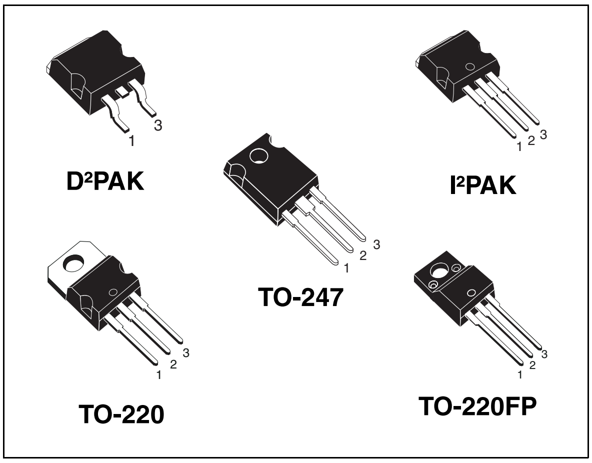
N-channel 600 V - 0.150 Ω - 19 A - D^2PAK - I^2PAK - TO-220/FP
TO-247, second generation MDmesh™ Power MOSFET

Features

Type	V_{DSS} (@Tjmax)	$R_{DS(on)}$ max	I_D
STB23NM60N	650 V	0.180 Ω	19 A
STI23NM60N			19 A
STF23NM60N			19 A (1)
STP23NM60N			19 A
STW23NM60N			19 A

1. Limited only by maximum temperature allowed

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Application

- Switching applications

Description

This series of devices is designed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

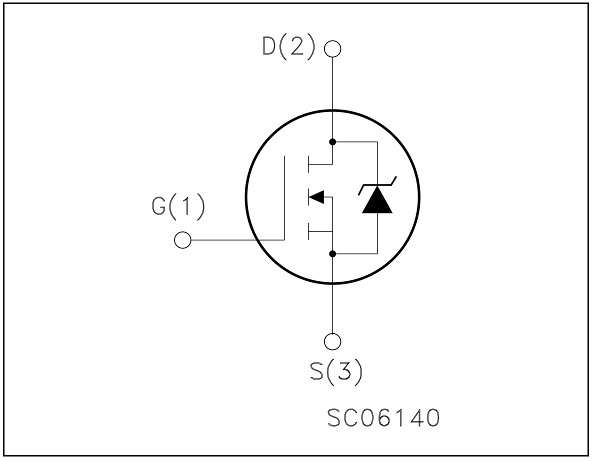


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB23NM60N	23NM60N	D²PAK	Tape and reel
STI23NM60N	23NM60N	I²PAK	Tube
STF23NM60N	23NM60N	TO-220FP	Tube
STP23NM60N	23NM60N	TO-220	Tube
STW23NM60N	23NM60N	TO-247	Tube